















**TMUX1072** JAJSF54C - APRIL 2018 - REVISED AUGUST 2019

# TMUX1072 過電圧検出および保護機能付きの2チャネル、2:1アナログ・ マルチプレクサ

## 特長

- 2.3V~5.5V の電源電圧範囲
- 電源オフ保護:

V<sub>CC</sub> = 0V のとき、I/O ピンは Hi-Z

- フォルト表示ピンによる 6V 過電圧および過熱検
- COMピンで 18V の過電圧保護 (OVP)
- V<sub>CC</sub> を超えて最高 5.5V までの信号に対応
- 低い R<sub>ON</sub>: 6Ω
- BW: 1.2GHz (標準値)
- C<sub>ON</sub>: 4.5pF (標準値)
- 低消費電力のディセーブル・モード
- 1.8V 互換のロジック入力
- JESD 22 を超える ESD 保護
  - 人体モデル (HBM) 2000V
- 2.00mm x 1.70mm の小型 QFN パッケージで供給

# 2 アプリケーション

- データ・アクイジション (DAQ)
- 現場用計測機器
- ビデオ監視
- HVAC システム
- リア・カメラ

# 3 概要

TMUX1072は高速、2チャネル、2:1のアナログ・スイッチ で、過電圧検出と電源オフ保護が内蔵されています。この デバイスは双方向で、2:1または1:2のスイッチとして使用 でき、Vccを超えて最高5.5Vまでの信号に対応できます。

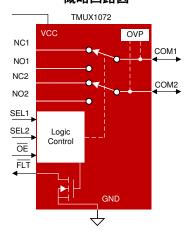
TMUX1072のI/Oピン上の保護機能は最高18Vまで耐え られ、自動シャットオフ回路により、スイッチより後にあるシ ステムの部品を損傷から保護できます。この保護機能は電 源シーケンスに使用されます。システム内の一部の基板 は、他の基板で信号の受信準備が整う前に電源オンにす ることができます。このデバイスは過電圧および過熱イベ ントを検出し、FLT ピン経由でオープン・ドレイン信号を出 力します。

#### 製品情報(1)

型番	パッケージ	本体サイズ(公称)
TM11V4070	UQFN (12)	2.00mm×1.70mm
TMUX1072	VSSOP (10)	3.00mm×5.00mm

(1) 提供されているすべてのパッケージについては、巻末の注文情報 を参照してください。

## 概略回路図





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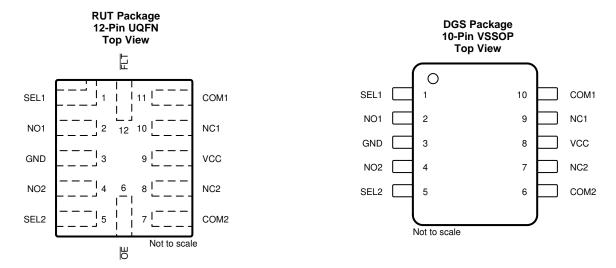
# 4 改訂履歴

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Revision B (June 2019) から Revision C に変更	Page
追加 Typical Characteristics curves for AC parameters	
Added the Application Curves section	18
Revision A (August 2018) から Revision B に変更	Page
<ul><li>「特長」を「COMピンで 0V~18V の過電圧保護 (OVP)」から「COMピンで 0V~6V の過電圧保護 (OVP)」に変</li></ul>	更
2018年4月発行のものから更新	Page
- • デバイスのステータスを「事前情報」から「量産データ」に変更	



# **5 Pin Configuration and Functions**



#### **Pin Functions**

	PIN		1/0	DESCRIPTION
NAME	RUT	DGS	I/O	DESCRIPTION
SEL1	1	1	I	Switch select 1
NO1	2	2	I/O	Signal path NO1
GND	3	3	GND	Ground
NO2	4	4	I/O	Signal path NO2
SEL2	5	5	I	Switch select 2
ŌĒ	6	-	I	Output enable (Active low)
COM2	7	6	I/O	Common signal path 2
NC2	8	7	I/O	Signal path NC2
VCC	9	8	PWR	Supply Voltage
NC1	10	9	I/O	Signal path NC1
COM1	11	10	I/O	Common signal path 1
FLT	12	-	0	Fault indicator output pin (Active low) - open drain. If feature is unused, pin may be left floating or connected to ground



## 6 Specifications

#### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1) (2)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage <sup>(3)</sup>		-0.5	6	V
	Input/Output DC voltage (COM1, COM2)	(3)	-0.5	20	V
V <sub>I/O</sub>	Input/Output DC voltage (NC1, NO1, NC2, NO2) (3)		-0.5	6	V
VI	Digital input voltage (SEL1, SEL2, <del>OE</del> )		-0.5	6	V
Vo	Digital output voltage (FLT)		-0.5	6	V
I <sub>K</sub>	Input-output port diode current (COM1, COM2,NC1, NO1, NC2, NO2)	V <sub>IN</sub> < 0	-50		mA
I <sub>IK</sub>	Digital <u>log</u> ic input clamp current (SEL1, SEL2, OE) (3)	V <sub>1</sub> < 0	-50		mA
I <sub>CC</sub>	Continuous current through VCC	•		100	mA
I <sub>GND</sub>	Continuous current through GND		-100		mA
T <sub>stg</sub>	Storage temperature		-65	150	°C
$T_{J}$	Operating Junction Temperature	·	-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## 6.2 ESD Ratings

			VALUE	UNIT
\/	V/ESD)	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±2000	V
V <sub>(ESD)</sub>		Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	±1000	V

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

			MIN	MAX	UNIT
$V_{CC}$	Supply voltage		2.3	5.5	V
V <sub>I/O</sub>		COM1, COM2	0	18	V
V <sub>I/O</sub>	Analog input/autaut	(NC1, NO1, NC2, NO2)	0	5.5	V
I <sub>I/O</sub>	<del>-</del>	COM1, COM2	-50	50	mA
I <sub>I/O</sub>		(NC1, NO1, NC2, NO2)	-50	50	mA
$V_{I}$	Digital input voltage	SEL1, SEL2, OE	0	5.5	V
Vo	Digital output voltage	FLT	0	5.5	V
I <sub>I/O</sub>	Analog input/output port continuous current	(COM1, COM2, NC1, NO1, NC2, NO2)	-50	50	mA
I <sub>OL</sub>	Digital output current			3	mA
T <sub>A</sub>	Operating free-air temperature		-40	125	°C
$T_J$	Junction temperature		-40	125	°С

<sup>(2)</sup> The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.

<sup>(3)</sup> All voltages are with respect to ground, unless otherwise specified.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



#### 6.4 Thermal Information

			TMU		
	THERMAL METRIC (1)			DGS (VSSOP)	UNIT
		12 PINS	10 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance		127	175	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance		55.5	61.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance		67.7	96.9	°C/W
ΨЈТ	Junction-to-top characterization parameter		1.6	8.2	°C/W
ΨЈВ	Junction-to-board characterization parameter		67.3	95.1	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

### 6.5 Electrical Characteristics

 $T_A = -40$ °C to +125°C ,  $V_{CC} = 2.3$  V to 5.5 V, GND = 0V, Typical values are at  $V_{CC} = 3.3$  V,  $T_A = 25$ °C, (unless otherwise noted)

P.A	ARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY					*	
V <sub>CC</sub>	Power supply voltage		2.3		5.5	V
	Active supply current	OE = 0 V SEL1, SEL2 = 0 V, 1.8 V or V <sub>CC</sub> 0 V < V <sub>I/O</sub> < 3.6 V		75	110	μΑ
Icc	Supply current during OVP condition	OE       0 V         SEL1, SEL2       0 V, 1.8 V or V <sub>CC</sub> V <sub>I/O</sub> > V <sub>POS_THLD</sub>		65	98	μΑ
I <sub>CC_PD</sub> <sup>(1)</sup>	Standby powered down supply current	OE = 1.8 V or V <sub>CC</sub> SEL1 = 0 V, 1.8 V, or VCC SEL2 = 0 V, 1.8 V, or VCC		3	10	μΑ
UVLO	Under Voltage Lock Out	V <sub>CC</sub> = rising and falling	1.65			V
DC Characteristics						
R <sub>ON</sub>	ON-state resistance	$V_{I/O} = 0 \text{ V to } V_{CC}$ $I_{SINK} = 8 \text{ mA}$ Refer to ON-State Resistance Figure		6	18	Ω
ΔR <sub>ON</sub>	ON-state resistance match between channels	$V_{I/O}$ = 0 V to $V_{CC}$ $I_{SINK}$ = 8 mA Refer to ON-State Resistance Figure		0.07	0.5	Ω
R <sub>ON (FLAT)</sub>	ON-state resistance flatness	$V_{I/O}$ = 0 V to $V_{CC}$ $I_{SINK}$ = 8 mA Refer to ON-State Resistance Figure		2.5	7	Ω

<sup>(1)</sup> Not tested for DGS package due to absence of FLT and OE pin.



# **Electrical Characteristics (continued)**

 $T_A = -40$ °C to +125°C ,  $V_{CC} = 2.3$  V to 5.5 V, GND = 0V, Typical values are at  $V_{CC} = 3.3$  V,  $T_A = 25$ °C, (unless otherwise noted)

noted)						
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
		$\begin{array}{l} V_{COM1/2}=0 \text{ V to } 5.5 \text{ V} \\ V_{CC}=2.3 \text{ V to } 5.5 \text{ V} \\ V_{NC1/2} \text{ or } V_{NO1/2}=5.5 \text{ V or } 0 \text{ V} \\ \text{Refer to Off Leakage Figure} \end{array}$		3.6	10	μΑ
		$V_{\text{COM1/2}} = 5.5 \text{ V}^{(2)}$ $V_{\text{CC}} = 5.5 \text{ V}$ $V_{\text{NC1/2}}$ or $V_{\text{NO1/2}} = 5.5 \text{ V}$ Refer to Off Leakage Figure			3	μΑ
		$\begin{array}{l} V_{COM1/2} = 3.6 \text{ V} ^{(2)} \\ V_{CC} = 3.3 \text{ V} \\ V_{NC1/2} \text{ or } V_{NO1/2} = 3.6 \text{ V} \\ \text{Refer to Off Leakage Figure} \end{array}$			2	μΑ
I <sub>OFF</sub>	I/O pin OFF leakage current	$\begin{aligned} &V_{COM1/2} = 5.5 \text{ V} \\ &V_{CC} = 0 \text{ V} \\ &V_{NC1/2} \text{ or } V_{NO1/2} = 5.5 \text{ V} \\ &\text{Refer to Off Leakage Figure} \end{aligned}$			15	μA
		$\begin{split} &V_{COM1/2} = 3.6 \text{ V} \\ &V_{CC} = 0 \text{ V} \\ &V_{NC1/2} \text{ or } V_{NO1/2} = 3.6 \text{ V} \\ &\text{Refer to Off Leakage Figure} \end{split}$			10	uA
		$\begin{split} &V_{COM1/2} = 1 \text{ V} \\ &V_{CC} = 0 \text{ V} \\ &V_{NC1/2} \text{ or } V_{NO1/2} = 1 \text{ V} \\ &\text{Refer to Off Leakage Figure} \end{split}$			2	uA
		$\begin{split} &V_{COM1/2} = 18 \text{ V} \\ &V_{CC} = 0 \text{ V}, 5.5 \text{ V} \\ &V_{NC1/2} \text{ or } V_{NO1/2} = 0 \text{ V} \\ &\text{Refer to Off Leakage Figure} \end{split}$		165	185	μΑ
	ON leakage augrent	$\begin{split} &V_{COM1/2} = 5.5 \text{ V} \\ &V_{CC} = 5.5 \text{ V} \\ &V_{NC1/2} \text{ and } V_{NO1/2} = \text{high-Z} \\ &\text{Refer to On Leakage Figure} \end{split}$		1.2	3.5	μΑ
I <sub>ON</sub>	ON leakage current	$\begin{split} &V_{COM1/2} = 0 \text{ V to 5.5 V} \\ &V_{CC} = 2.3\text{-}5.5 \text{ V} \\ &V_{NC1/2} \text{ and } V_{NO1/2} = \text{high-Z} \\ &\text{Refer to On Leakage Figure} \end{split}$			11.5	μΑ
Digital Characteris	itics					
$V_{IH}$	Input logic high	SEL1, SEL2, OE	1.45			V
V <sub>IL</sub>	Input logic low	SEL1, SEL2, OE			0.5	V
V <sub>OL</sub>	Output logic low	FLT I <sub>OL</sub> = 3 mA			0.3	V
I <sub>IH</sub>	Input high leakage current	SEL1, SEL2, $\overline{\text{OE}}$ = 1.8 V, V <sub>CC</sub>	-1	2	5	μΑ
I <sub>IL</sub>	Input low leakage current	SEL1, SEL2, $\overline{\text{OE}}$ = 0 V	-1	±0.2	1	μΑ
R <sub>PD</sub>	Internal pull-down resistor on digital input pins	SEL1, SEL2  OE		6	12 6	MΩ MΩ
C <sub>I</sub> (3)	Digital input capacitance	SEL1, SEL2 = 0 V, 1.8 V or VCC f = 1 MHz		8		pF
Protection and De	tection	1				
V <sub>OVP_TH</sub>	OVP positive threshold		5.55	5.8	6.0	V
V <sub>OVP_HYST</sub> (3)	OVP threshold hysteresis		40	100	300	mV
		1	-			

Not tested on COM1/2 pins for DGS package due to the absence of OE pin Specified by design, not tested in production.

<sup>(3)</sup> 



# **Electrical Characteristics (continued)**

 $T_A = -40^{\circ}C$  to +125°C ,  $V_{CC} = 2.3$  V to 5.5 V, GND = 0V, Typical values are at  $V_{CC} = 3.3$  V,  $T_A = 25^{\circ}C$ , (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
T <sub>SD_HYST</sub> <sup>(3)</sup>	Thermal Shutdown Hysteresis		3		8	°C
T <sub>OTD_TH</sub> <sup>(3)</sup>	Overtemperature detection threshold		135		165	°C
V <sub>CLAMP_V</sub> <sup>(3)</sup>	Maximum voltage to appear	$V_{COM1/2} = 0$ to 18 V $t_{RISE}$ and $t_{FALL}(10\%$ to 90 %) = 100 ns $R_L = Open$ Switch on or off $\overline{OE} = 0$ V	0		9.6	V
	on NC1/2 and NO1/2 pins during OVP scenario	$\begin{aligned} &V_{COM1/2} = 0 \text{ to } 18 \text{ V} \\ &t_{RISE} \text{ and } t_{FALL} (10\% \text{ to } 90 \text{ \%}) = 100 \text{ ns} \\ &R_L = 50\Omega \\ &\underline{\text{Switch on or off}} \\ &\overline{\text{OE}} = 0 \text{ V} \end{aligned}$	0		9.0	V
t <sub>EN_OVP</sub> (3)	OVP enable time	$R_{PU}$ = 10 k $\Omega$ to VCC ( $\overline{FLT}$ ) $C_L$ = 35 pF Refer to OVP Timing Diagram Figure		0.6	3	μS
t <sub>REC_OVP</sub> (3)	OVP recovery time	$R_{PU}$ = 10 k $\Omega$ to VCC ( $\overline{FLT}$ ) $C_L$ = 35 pF Refer to OVP Timing Diagram Figure		1.5	5	μ\$



## 6.6 Dynamic Characteristics

 $T_A = -40$ °C to +125°C ,  $V_{CC} = 2.3$  V to 5.5V, GND = 0V, Typical values are at  $V_{CC} = 3.3$  V,  $T_A = 25$ °C, (unless otherwise noted)

PARAMETER <sup>(1)</sup>		TEST CONDITION	MIN	TYP	MAX	UNIT	
	COM1, COM2 off capacitance	$\frac{V_{COM1/2}}{OE} = 0$ or 3.3 V, $\frac{V_{COM1/2}}{OE} = V_{CC}$ f = 240  MHz	Switch OFF	1.2	4.0	6.2	pF
C <sub>OFF</sub>	NC1, NO1, NC2, NO2 off capacitance	$\begin{tabular}{ll} $V_{COM1/2}=0$ or $3.3$ V,\\ \hline OE = V_{CC}$ or $\overline{OE}=0$ V with SEL1,\\ SEL2$ (switch not selected)\\ f = 240$ MHz \\ \end{tabular}$	Switch OFF or not selected	1.2	4.0	6.2	pF
C <sub>ON</sub>	COM1, COM2, NC1, NO1, NC2, NO2 on capacitance	$V_{COM1/2} = 0$ or 3.3 V, f = 240 MHz	Switch ON	1.4	4.0	6.2	pF
O <sub>ISO</sub>	Differential off isolation	RL = $50 \Omega$ CL = $5 pF$ f = $100 kHz$ Refer to Off Isolation Figure	Switch OFF		-80		dB
	Differential of Isolation	RL = $50 \Omega$ CL = $5 pF$ f = $240 MHz$ Refer to Off Isolation Figure	Switch OFF		-22		dB
X <sub>TALK</sub>	Channel to Channel crosstalk	RL = $50 \Omega$ CL = $5 pF$ f = $100 kHz$ Refer to Crosstalk Figure	Switch ON		-90		dB
BW	Bandwidth	RL = 50 Ω; Refer to BW and Insertion Loss Figure	Switch ON		1.2		GHz
I <sub>LOSS</sub>	Insertion loss	RL = 50 Ω f = TBD MHz; Refer to BW and Insertion Loss Figure	Switch ON		-0.8		dB

<sup>(1)</sup> Specified by design, not tested in production.

# 6.7 Timing Requirements

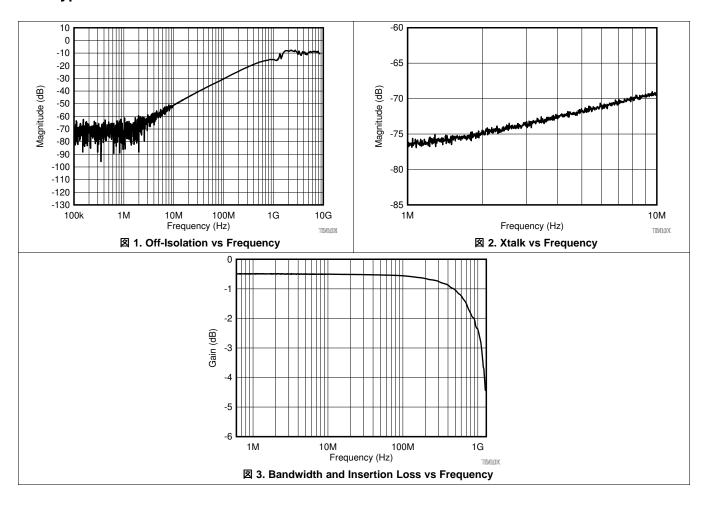
 $T_A = -40$ °C to +125°C ,  $V_{CC} = 2.3$  V to 5.5V, GND = 0V, Typical values are at  $V_{CC} = 3.3$  V,  $T_A = 25$ °C, (unless otherwise noted)

	PARAMETER <sup>(1)</sup>	TEST CONDITI	ONS	MIN	NOM	MAX	UNIT
t <sub>switch</sub>	Switching time between channels (SEL1, SEL2 to output)	V <sub>NC</sub> = 0.8 V Refer to Tswitch Timing Figure			0.9	1	μs
t <sub>on</sub>	Device turn on time (OE to output)	V <sub>NC</sub> = 0.8 V Refer to Ton and Toff Figure	D 50.0		200	250	μs
t <sub>off</sub>	Device turn off time (OE to output)	V <sub>NC</sub> = 0.8 V Refer to Ton and Toff Figure	$R_L = 50 \Omega,$ $C_L = 5 pF,$ $V_{CC} = 2.3 V to 5.5 V$		1	10	μs
t <sub>off_Vcc</sub>	Device turn off time $V_{\text{CC}}$ to Switch off	$V_{NC}$ = 0.8 V Refer to Ton and Toff Figure Ramp rate $V_{CC}$ = 2.3 V to 0 V 250µs				250	μs
t <sub>SK(P)</sub>	Skew of opposite transitions of same output (between COM1 and COM2) <sup>(1)</sup>	V <sub>COM1/2</sub> = V <sub>CC</sub> Refer to Tsk Figure	$R_L = 50 \Omega,$ $C_L = 1 pF,$ $V_{CC} = 2.3 V to 5.5 V$		9	50	ps
t <sub>pd</sub>	Propagation delay <sup>(1)</sup>	V <sub>COM1/2</sub> = V <sub>CC</sub> Refer to Tpd Figure	$R_L = 50 \Omega,$ $C_L = 5 pF,$ $V_{CC} = 2.3 V to 5.5 V$		130	200	ps

<sup>(1)</sup> Specified by design, not tested in production.

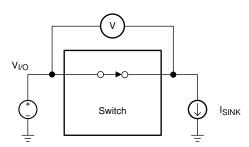


# 6.8 Typical Characteristics





# 7 Parameter Measurement Information



Channel ON,  $R_{ON} = V/I_{SINK}$ 

# 図 4. ON-State Resistance (R<sub>ON</sub>)

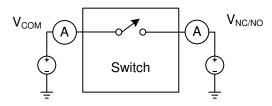


図 5. Off Leakage

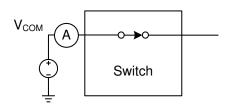
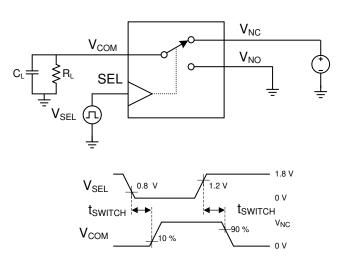


図 6. On Leakage

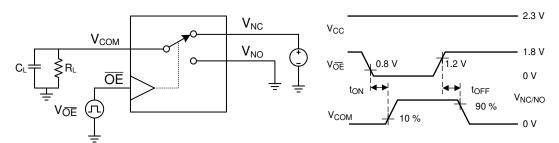


- (1) All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50~\Omega$ ,  $t_r < 500~ps$ ,  $t_f < 500~ps$ .
- (2) C<sub>L</sub> includes probe and jig capacitance.

図 7. t<sub>SWITCH</sub> Timing



# **Parameter Measurement Information (continued)**



- (1) All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50 \Omega$ ,  $t_r < 500$  ps,  $t_f < 500$  ps.
- (2) C<sub>L</sub> includes probe and jig capacitance.

# 2 8. $t_{ON}$ , $t_{OFF}$ for $\overline{OE}$

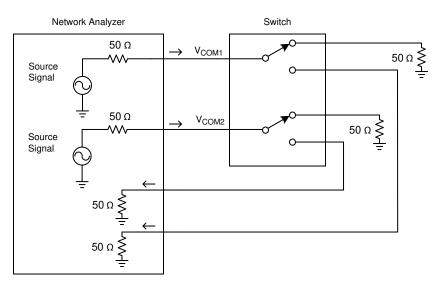


図 9. Off Isolation

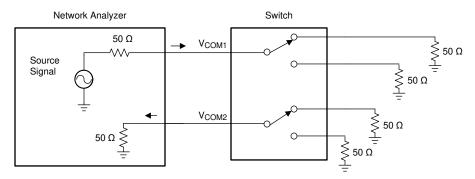


図 10. Cross Talk



# **Parameter Measurement Information (continued)**

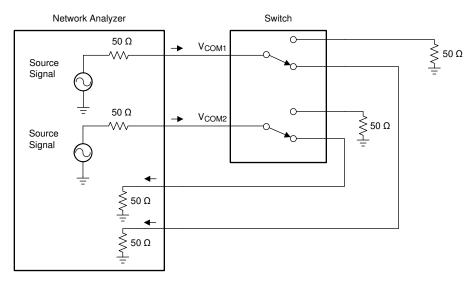
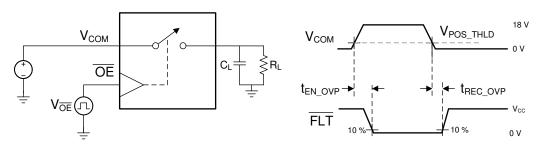
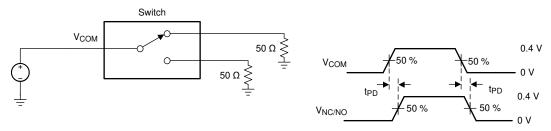


図 11. BW and Insertion Loss



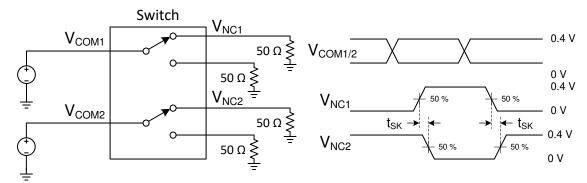


- (1) All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50 \Omega$ ,  $t_r < 500$  ps,  $t_f < 500$  ps.
- (2) C<sub>L</sub> includes probe and jig capacitance.

図 13. t<sub>PD</sub>



# **Parameter Measurement Information (continued)**



- (1) All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50~\Omega$ ,  $t_r < 500~ps$ ,  $t_f < 500~ps$ .
- (2) C<sub>L</sub> includes probe and jig capacitance.

図 14. t<sub>SK</sub>



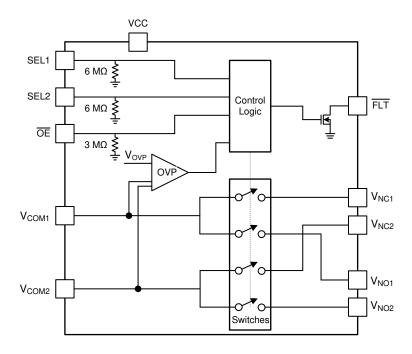
### 8 Detailed Description

#### 8.1 Overview

The TMUX1072 is a high speed, 2-channel 2:1 analog switch with overvoltage protection. The device is bidirectional and can be used as a dual 2:1 or 1:2 switch, but OVP only applies to the COM pins. The device also contains a fault indicator pin which can signal to the system of either an over voltage or over temperature event.

The device maintains excellent signal integrity through the optimization of both  $R_{ON}$  and BW while protecting the system with up to 18 V OVP protection. The OVP implementation is designed to protect sensitive system components behind the switch that cannot survive fault conditions.

## 8.2 Functional Block Diagram





#### 8.3 Feature Description

#### 8.3.1 Powered-off Protection

When the TMUX1072 is powered off the I/Os of the device remain in a high-Z state. The crosstalk, off-isolation, and leakage remain within the *Electrical Specifications* 

This prevents errant voltages from reaching the rest of the system and maintains isolation when the system is powering up.

#### 8.3.2 Overvoltage Detection

When a voltage on the COM pin exceeds the  $V_{OVP\_TH}$ , the open drain output  $\overline{FLTpin}$  pulls the pin low to indicate an overvoltage event has been detected. The open drain output will release the  $\overline{FLT}$  pin when the voltage on the COM pin returns below the  $V_{OVP\_TH}$ .

#### 8.3.3 Overtemperature Detection

When the junction temperature of the device exceeds the overtemperature detection threshold  $T_{OTD\_TH}$ , the open drain output  $\overline{FLT}$  pin pulls the pin low to indicate an overtemperature event has been detected. The open drain output releases the  $\overline{FLT}$  pin when the junction temperature returns below the  $T_{OTD\_TH}$ .

#### 8.3.4 Overvoltage Protection

The OVP of the TMUX1072 is designed to protect the system from overvoltage conditions up to 18 V on the COM1 and COM2 pins. This protection is valid even if Vcc = 0V. ☒ 15 depicts an event where up to 18 V could appear on COM1 and COM2 that could pass through the device and damage components behind the device.

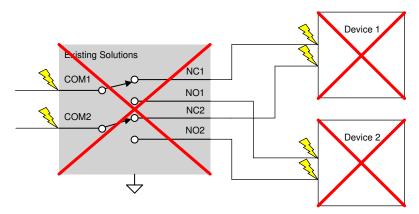


図 15. Existing Solution Being Damaged by a Short, 18 V

The TMUX1072 opens the switches and protect the rest of the system by blocking the 18 V as depicted in ⊠ 16.



# **Feature Description (continued)**

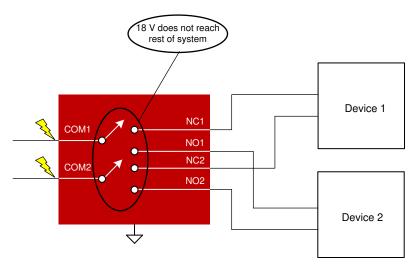


図 16. Protecting During a 18-V Short

☑ 17 is a waveform showing the voltage on the pins during an overvoltage scenario.

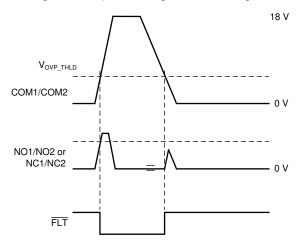


図 17. Overvoltage Protection Waveform, 18 V

## 8.4 Device Functional Modes

### 8.4.1 Pin Functions

表 1. Function Table

ŌĒ	SEL1	SEL2	COM1 Connection	COM2 Connection
Н	X	X	High-Z	High-Z
L	L	L	COM1 to NC1	COM2 to NC2
L	L	Н	COM1 to NC1	COM2 to NO2
L	Н	L	COM1 to NO1	COM2 to NC2
L	Н	Н	COM1 to NO1	COM2 to NO2



# 9 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

#### 9.1 Application Information

There are many applications in which processors and microcontrollers have a limited number of I/Os. This IC can effectively expand the limited number of I/Os by switching between multiple signal paths in order to interface them to a single processor or microcontroller. The device can also be used to connect a single microcontroller to two signal paths. With independent control of the two switches using SEL1 and SEL2, TMUX1072 can be used to cross switch single ended signals.

## 9.2 Typical Application

The TMUX1072 is used to switch signals between the high speed signal paths that may be exposed to a connector or near a bus which could experience an overvoltage condition. The TMUX1072 has internal pull-down resistors on SEL1, SEL2, and OE. The pull-down on SEL1 and SEL2 pins ensure the NC1/NC2 channel is selected by default. The pull-down on OE enables the switch when power is applied.

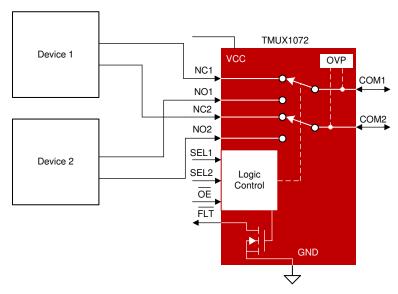


図 18. Typical TMUX1072 Application

#### 9.2.1 Design Requirements

The TMUX1072 has internal pull-down resistors on SEL1, SEL2, and  $\overline{\text{OE}}$ , so no external resistors are required on the logic pins. The internal pull-down resistor on SEL1 and SEL2 pins ensures the NC1 and NC2 channels are selected by default. The internal pull-down resistor on  $\overline{\text{OE}}$  enables the switch when power is applied to VCC.

The  $\overline{\text{FLT}}$  indicator output pin is an open drain output that will require an external pull-up resistor for the overvoltage and overtemperature condition to be detected. If feature is unused,  $\overline{\text{FLT}}$  pin may be left floating or connected to ground

#### 9.2.2 Detailed Design Procedure

The TMUX1072 can be properly operated without any external components. However, TI recommends that unused signal pins must be connected to ground through a  $50-\Omega$  resistor to prevent signal reflections back into the device. TI does recommend a 100-nF bypass capacitor placed close to TMUX1072 VCC pin.

## **Typical Application (continued)**

#### 9.2.3 Application Curves

Bandwidth is defined as the range of frequencies that are attenuated by less than 3 dB when the input is applied to the source pin of an on-channel, and the output is measured at the drain pin of the TMUX1072. ☒ 19 shows the bandwidth of TMUX1072.

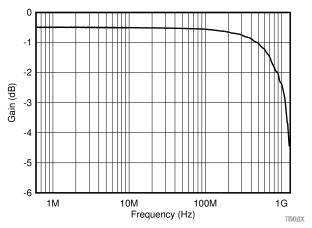


図 19. Bandwidth and Insertion Loss vs Frequency

## 10 Power Supply Recommendations

Power to the device is supplied through the VCC pin. TI recommends placing a 100-nF bypass capacitor as close to the supply pin VCC as possible to help smooth out lower frequency noise to provide better load regulation across the frequency spectrum.

#### 11 Layout

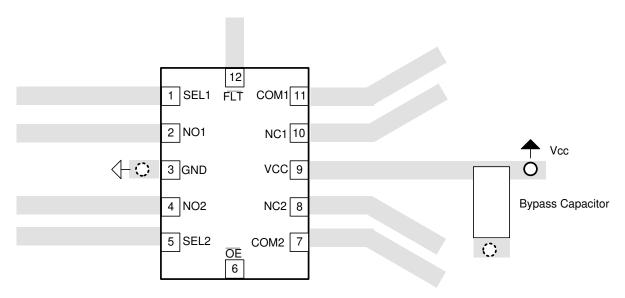
#### 11.1 Layout Guidelines

- 1. Place supply bypass capacitors as close to VCC pin as possible and avoid placing the bypass caps near the signal traces.
- 2. The high-speed traces should always be of equal length and must be no more than 4 inches; otherwise, the eye diagram performance may be degraded.
- 3. Route the high-speed signals using a minimum of vias and corners which will reduce signal reflections and impedance changes. When a via must be used, increase the clearance size around it to minimize its capacitance. Each via introduces discontinuities in the transmission line of the signal and increases the chance of picking up interference from the other layers of the board. Be careful when designing test points on twisted pair lines; through-hole pins are not recommended.
- 4. When it becomes necessary to turn 90°, use two 45° turns or an arc instead of making a single 90° turn. This reduces reflections on the signal traces by minimizing impedance discontinuities.
- 5. Do not route signal traces under or near crystals, oscillators, clock signal generators, switching regulators, mounting holes, magnetic devices, or IC's that use or duplicate clock signals.
- 6. Avoid stubs on the high-speed signals because they cause signal reflections.
- 7. Route all high-speed signal traces over continuous planes (VCC or GND), with no interruptions.
- 8. Avoid crossing over anti-etch, commonly found with plane splits.
- 9. For high frequency systems, a printed circuit board with at least four layers is recommended: two signal layers separated by a ground layer and a power layer. The majority of signal traces should run on a single layer, preferably Signal 1. Immediately next to this layer should be the GND plane, which is solid with no cuts. Avoid running signal traces across a split in the ground or power plane. When running across split planes is unavoidable, sufficient decoupling must be used. Minimizing the number of signal vias reduces EMI by reducing inductance at high frequencies. For more information on layout guidelines, see High Speed Layout Guidelines (SCAA082)



# 11.2 Layout Example





Not to scale

図 20. Layout Example



# 12 デバイスおよびドキュメントのサポート

# 12.1 ドキュメントのサポート

#### 12.1.1 関連資料

関連資料については、以下を参照してください。

- 『高速レイアウト・ガイドライン』アプリケーション・レポート
- 『高速インターフェイスのレイアウト・ガイドライン』

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#### 12.3 コミュニティ・リソース

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#### 12.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

### 13 メカニカル、パッケージ、および注文情報

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www.ti.com 23-May-2025

#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
TMUX1072DGSR	Active	Production	VSSOP (DGS)   10	2500   LARGE T&R	Yes	NIPDAUAG   SN	Level-1-260C-UNLIM	-40 to 125	1A9
TMUX1072DGSR.A	Active	Production	VSSOP (DGS)   10	2500   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	1A9
TMUX1072RUTR	Active	Production	UQFN (RUT)   12	3000   LARGE T&R	Yes	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	1BU
TMUX1072RUTR.A	Active	Production	UQFN (RUT)   12	3000   LARGE T&R	Yes	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	1BU

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

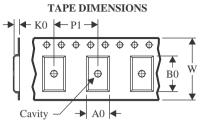
<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

# **PACKAGE MATERIALS INFORMATION**

www.ti.com 5-Nov-2024

### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device		Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TMUX1072DGSR	VSSOP	DGS	10	2500	330.0	12.4	5.25	3.35	1.25	8.0	12.0	Q1
TMUX1072RUTR	UQFN	RUT	12	3000	180.0	9.5	1.9	2.2	0.7	4.0	8.0	Q1

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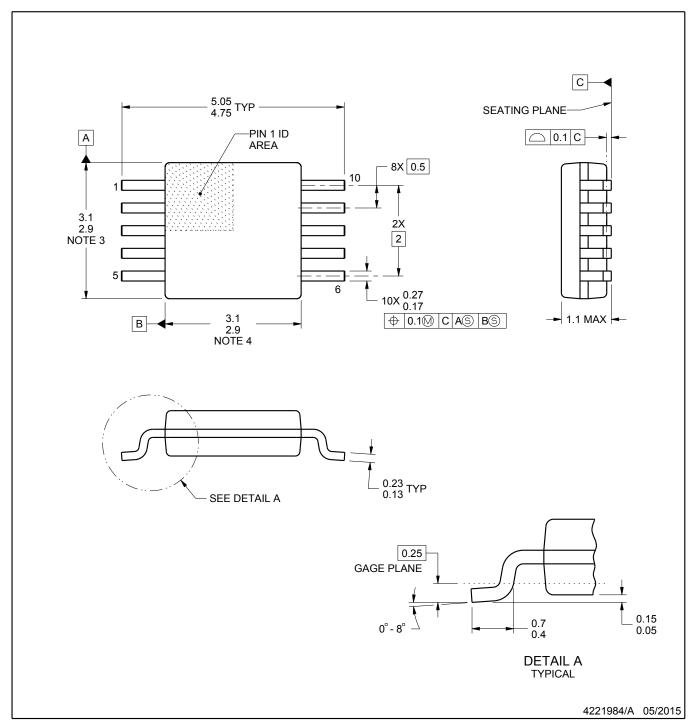


#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TMUX1072DGSR	VSSOP	DGS	10	2500	366.0	364.0	50.0
TMUX1072RUTR	UQFN	RUT	12	3000	189.0	185.0	36.0



SMALL OUTLINE PACKAGE



#### NOTES:

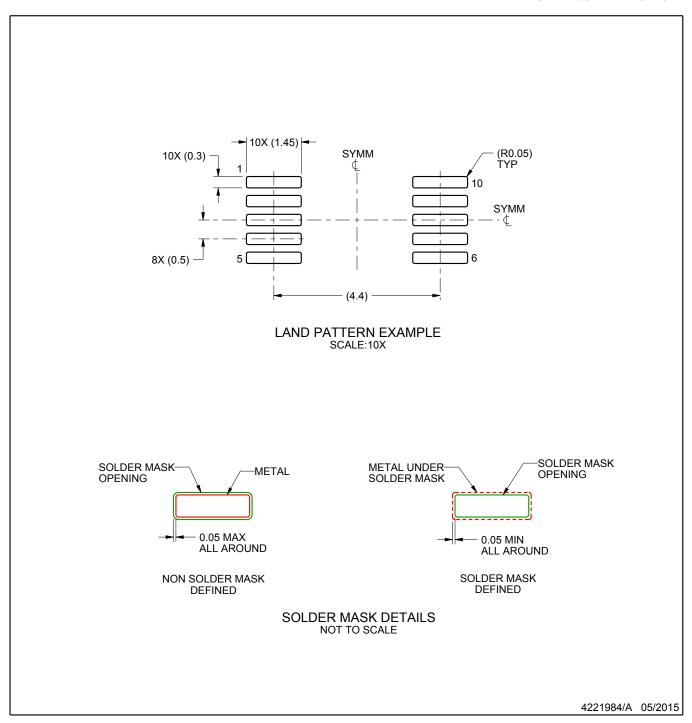
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187, variation BA.



SMALL OUTLINE PACKAGE



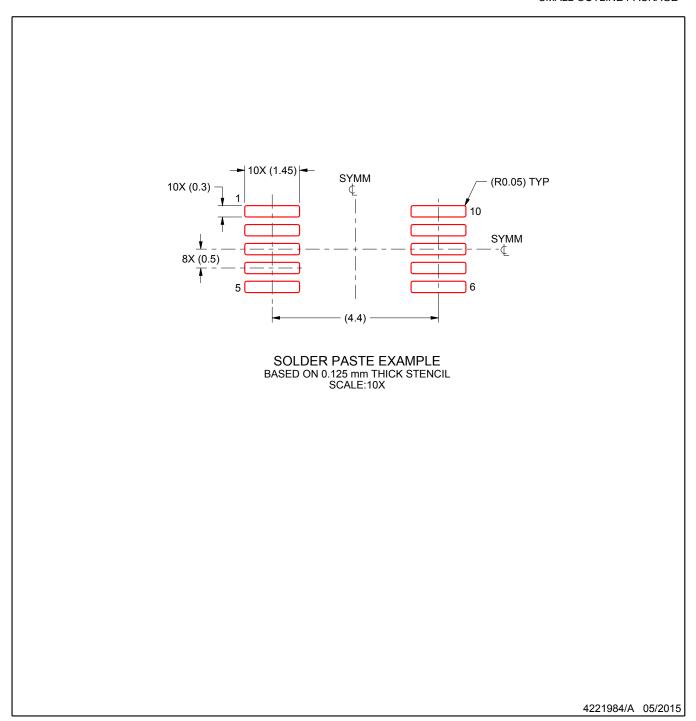
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



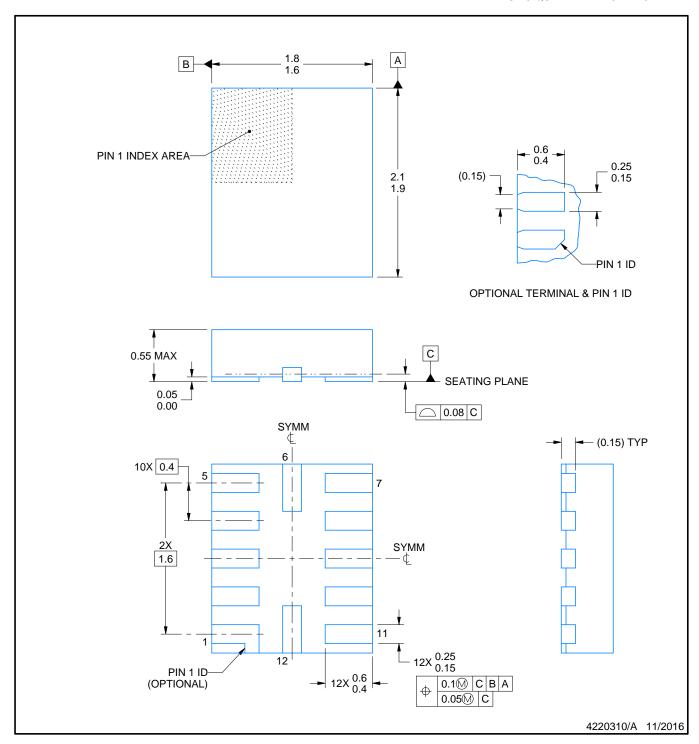
NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





PLASTIC QUAD FLATPACK - NO LEAD

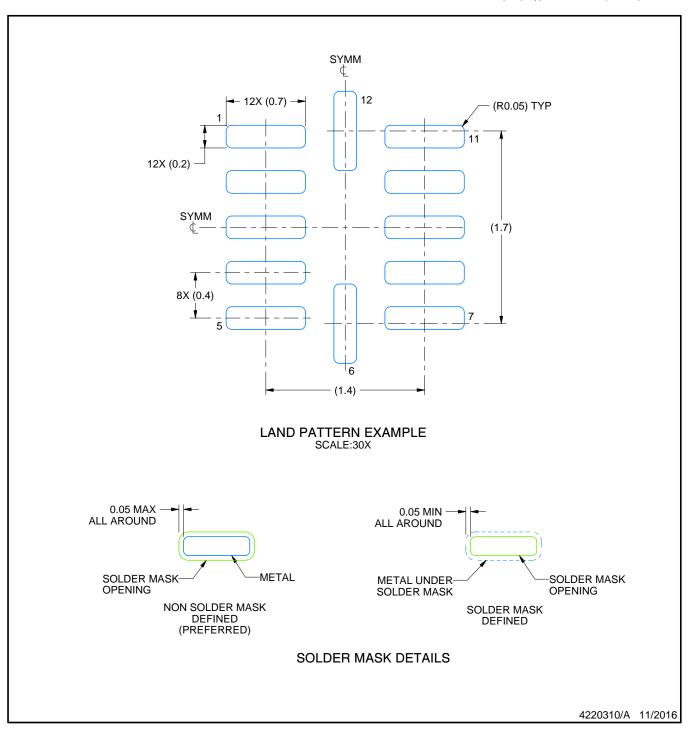


#### NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
   This drawing is subject to change without notice.



PLASTIC QUAD FLATPACK - NO LEAD

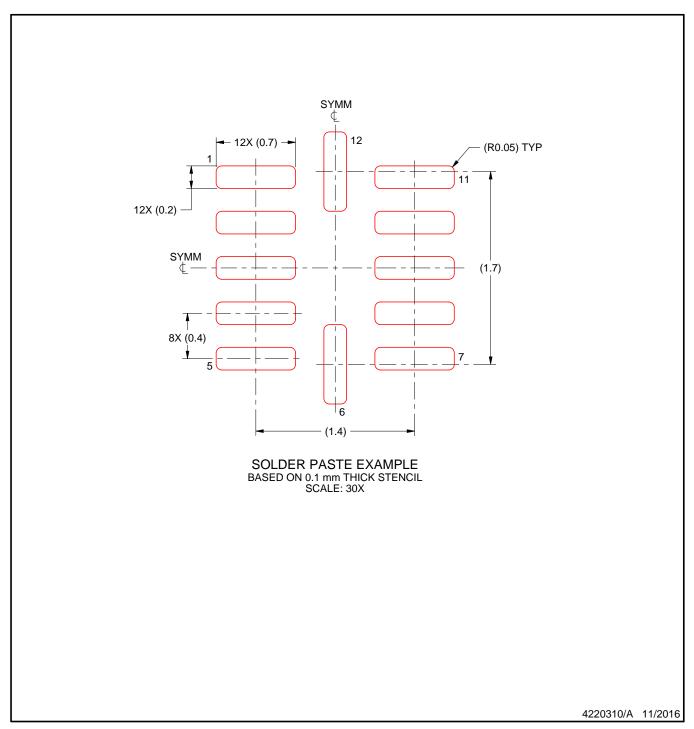


NOTES: (continued)

3. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).



PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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